

B1 Cont'd

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure higher than 1 atm in a temperature lower than a strain point of said glass substrate.

B2 sub c2

9. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure higher than 1 atm in a temperature of 500 to 650°C.

B3 sub c3

17. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure higher than 1 atm in a temperature lower than a strain point of said glass substrate.

B4 sub c4

25. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film; and

forming an insulating film adjacent to said crystallized semiconductor film by plasma CVD; and

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control

forming gate electrodes adjacent to said insulating film,
wherein said method further comprises a step of oxidizing the
crystallized semiconductor film to be active layers of said thin film transistors at a
pressure higher than 1 atm in a temperature lower than a strain point of said glass
substrate.

B5
SubC5

33. (Amended) A method of manufacturing a display device having a
plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating
surface;

crystallizing said semiconductor film; and

forming an insulating film adjacent to said crystallized semiconductor
film by plasma CVD; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the
crystallized semiconductor film to be active layers of said thin film transistors at a
pressure higher than 1 atm in a temperature of 500 to 650°C.

B6
SubC6

41. (Amended) A method of manufacturing a display device having a
plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free
glass substrate;

crystallizing said semiconductor film; and

forming an insulating film adjacent to said crystallized semiconductor
film by plasma CVD; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the
crystallized semiconductor film to be active layers of said thin film transistors at a

pressure higher than 1 atm in a temperature lower than a strain point of said glass substrate.

49. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms,

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

56. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms,

wherein said oxidizing the semiconductor film is performed in a temperature of 500 to 650°C.

63. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

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contd*

crystallizing said semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms for electrically isolating said plurality of thin film transistors one another,

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

*Sub C 10
B10*

70. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms, and

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.

*Sub C 10
B11*

78. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon on an insulating surface;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film; and

forming gate electrodes adjacent to said insulating film,

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contd

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms, and

wherein said oxidizing the semiconductor film is performed in a temperature of 500 to 650°.

SubC12
B12

86. (Amended) A method of manufacturing a display device having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over an alkali-free glass substrate;

crystallizing said semiconductor film;

forming an insulating film adjacent to said crystallized semiconductor film; and

forming gate electrodes adjacent to said insulating film,

wherein said method further comprises a step of oxidizing the crystallized semiconductor film to be active layers of said thin film transistors at a pressure of 1 to 15 atms, and

wherein said oxidizing the semiconductor film is performed in a temperature lower than a strain point of said glass substrate.